

# Anomalous acoustoelectric transport in graphene quantum Hall regimes

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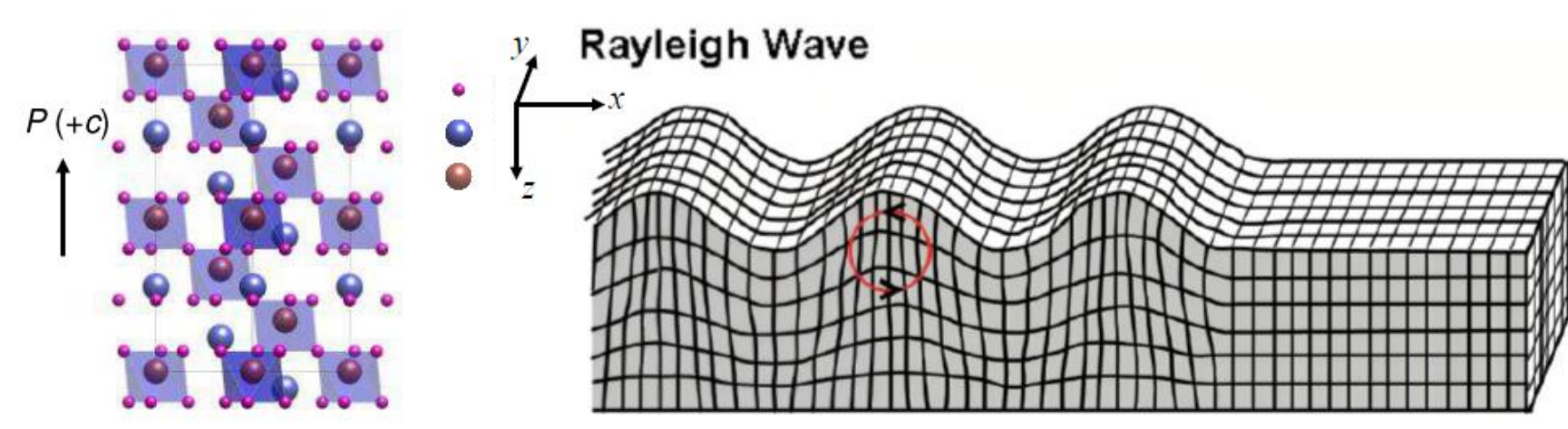
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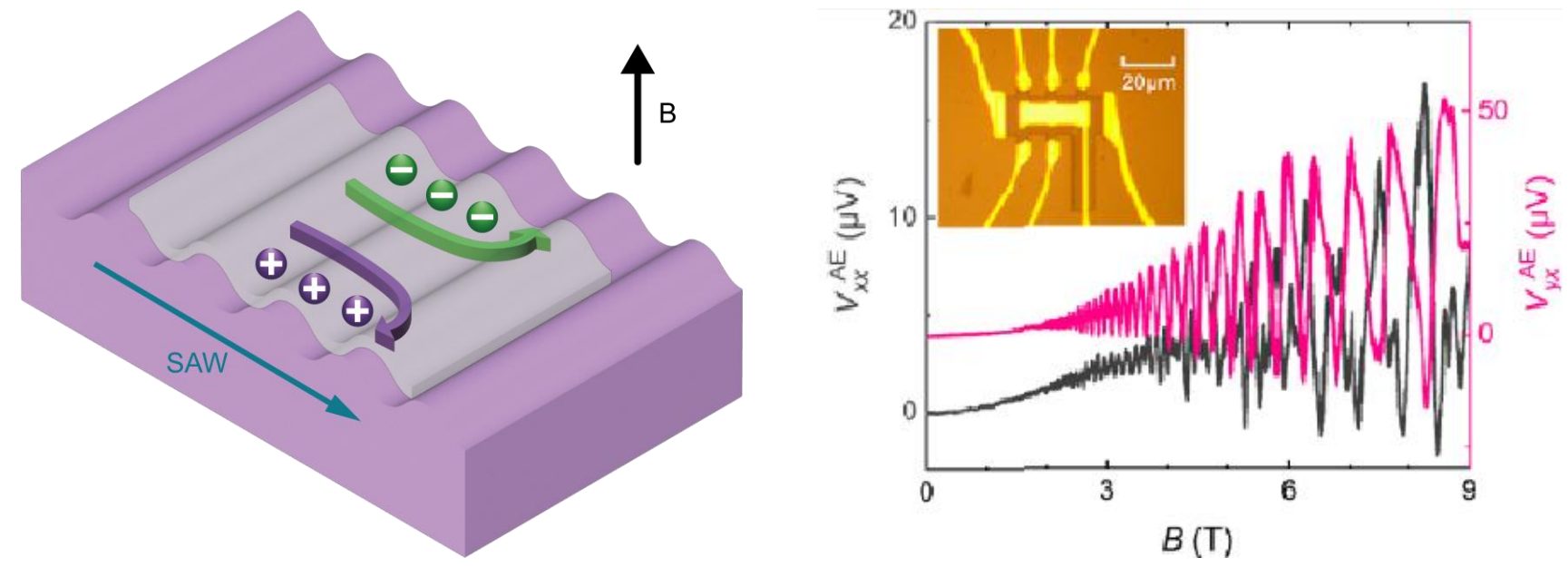
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## Introduction

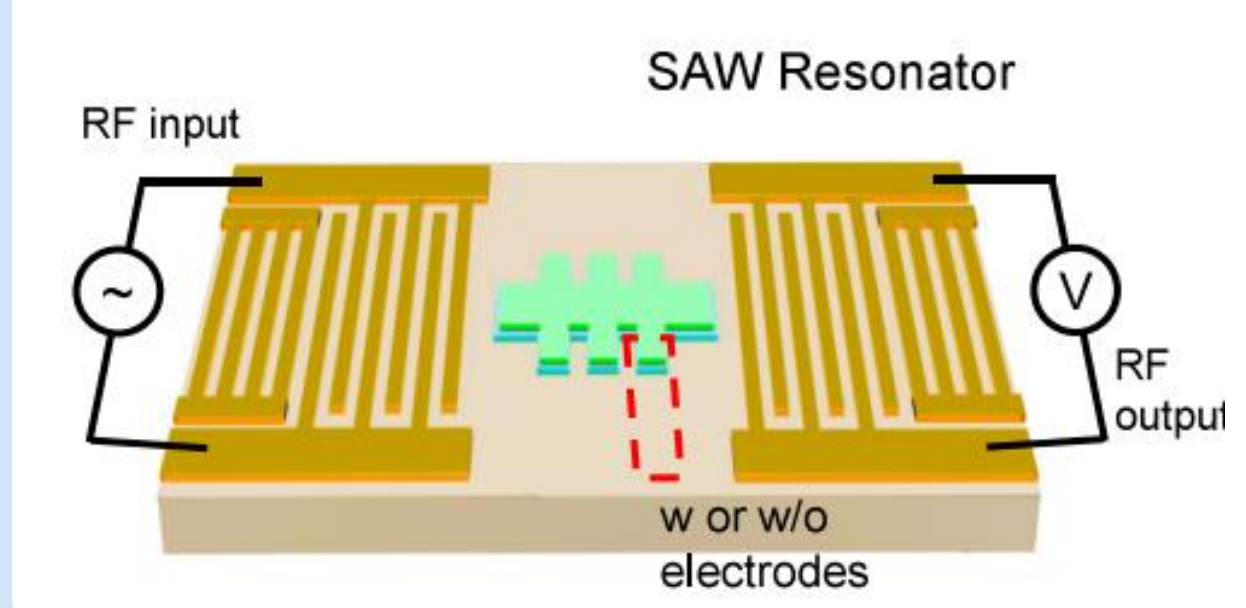
Piezoelectrically generated surface acoustic waves (SAWs)



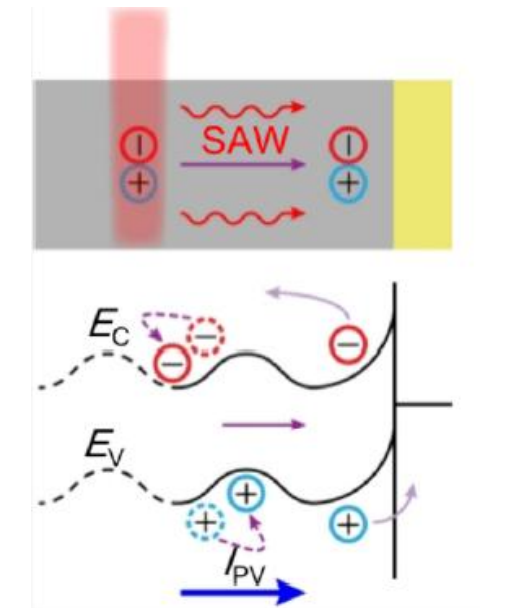
Acoustoelectric (AE) transport probes quantum oscillations



Acoustic attenuation unveils quantum oscillations

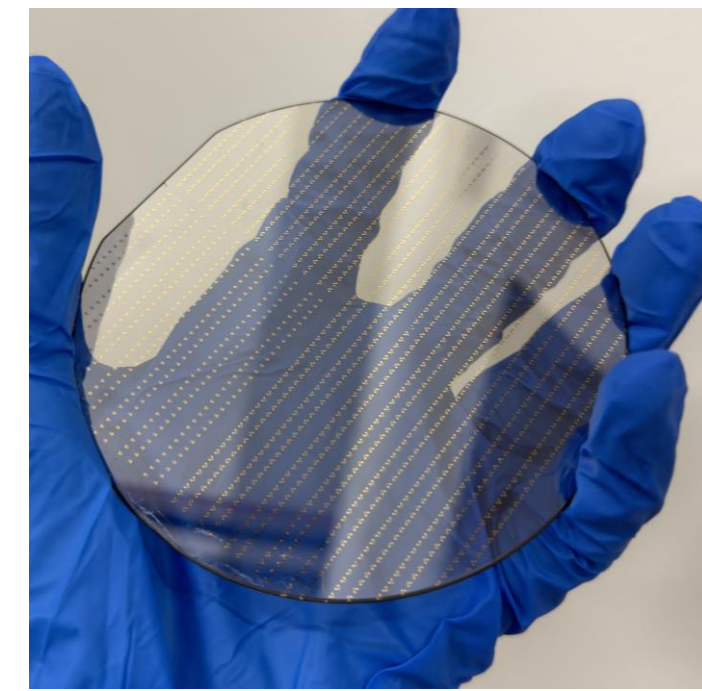


Acousto-drag photovoltaic effect

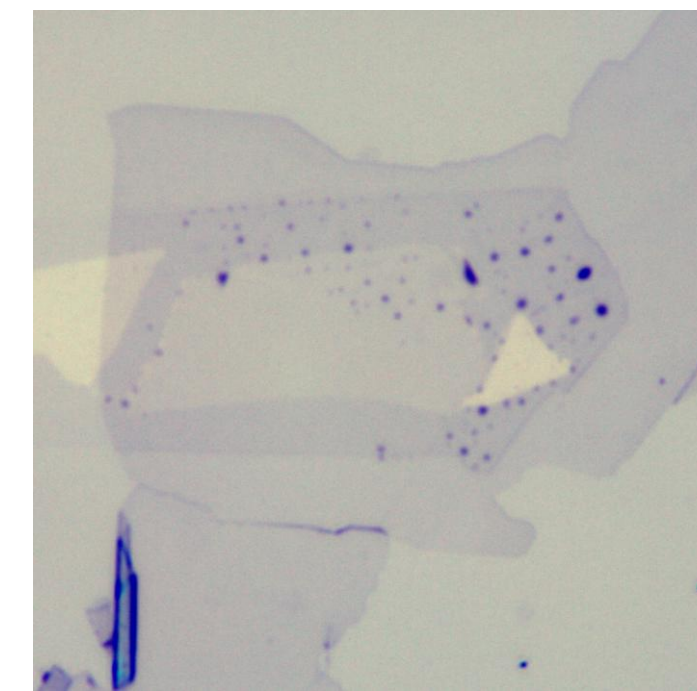


## Methods

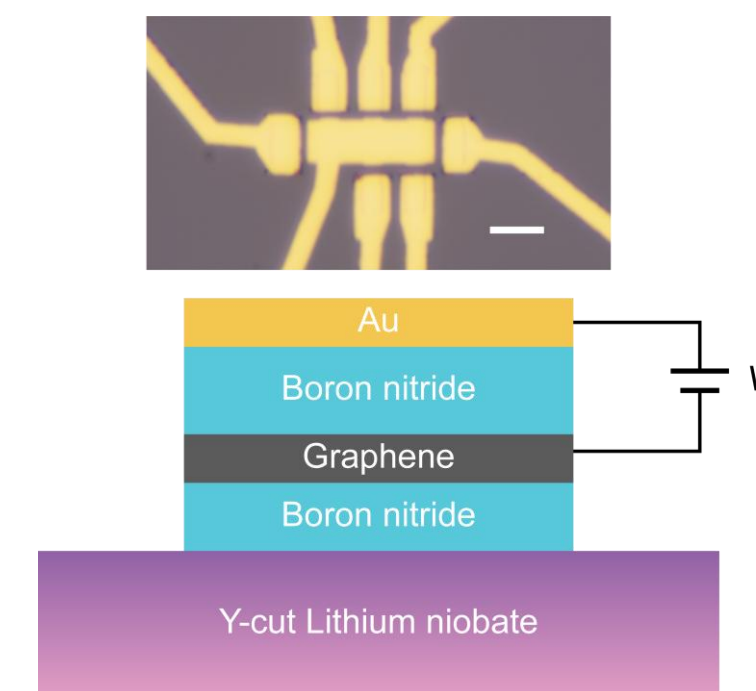
### Device fabrication



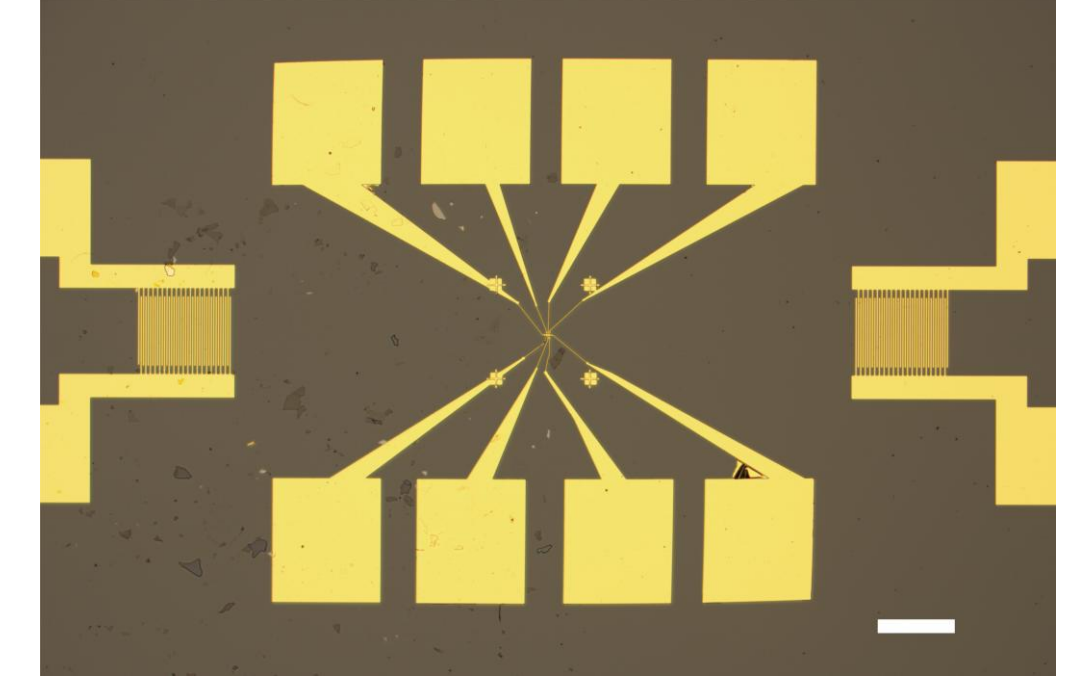
Delay-line IDTs on Y-cut LiNbO<sub>3</sub>



Standard dry-transfer technique hBN/graphene/hBN heterostructures



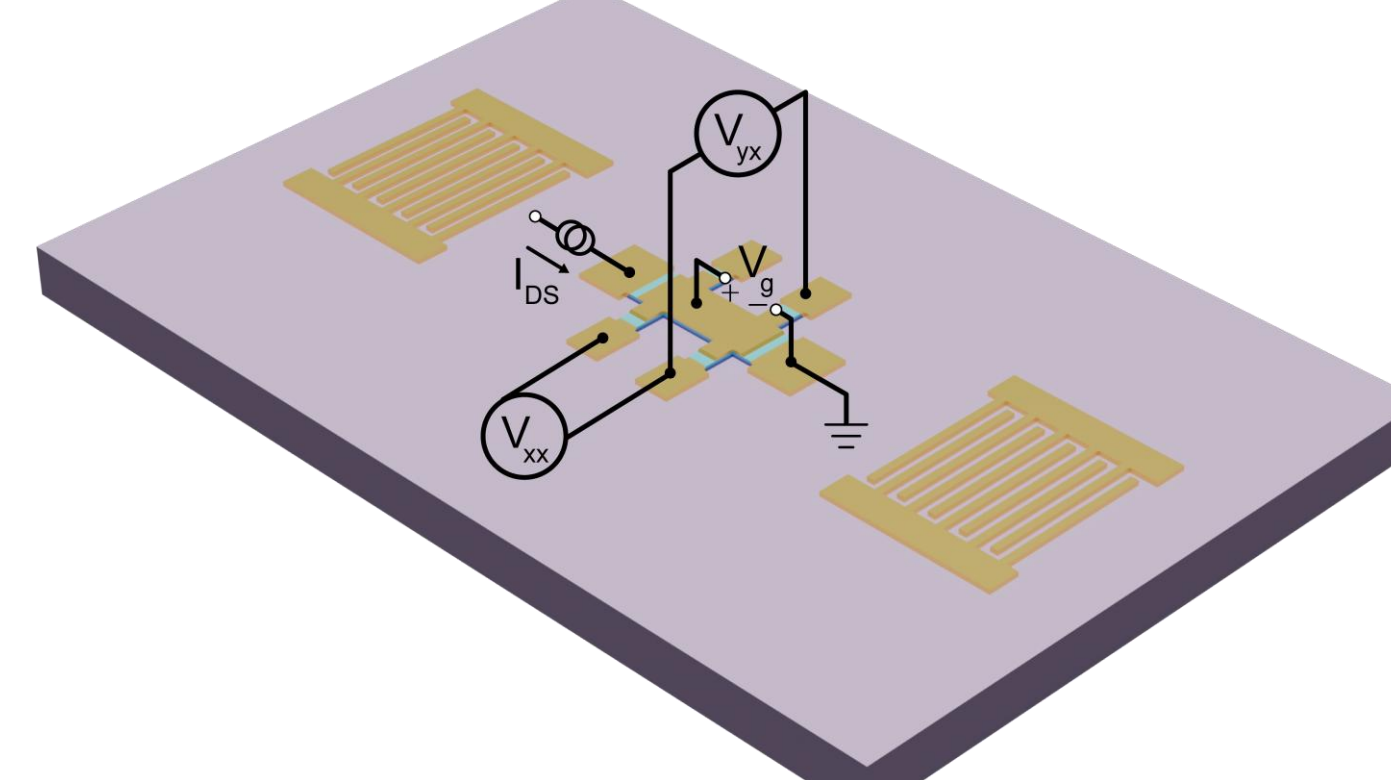
Electron beam lithography (EBL) - Electron beam evaporation (EBE) - EBL - Reactive ion beam etching (RIE) - EBL - RIE - EBE



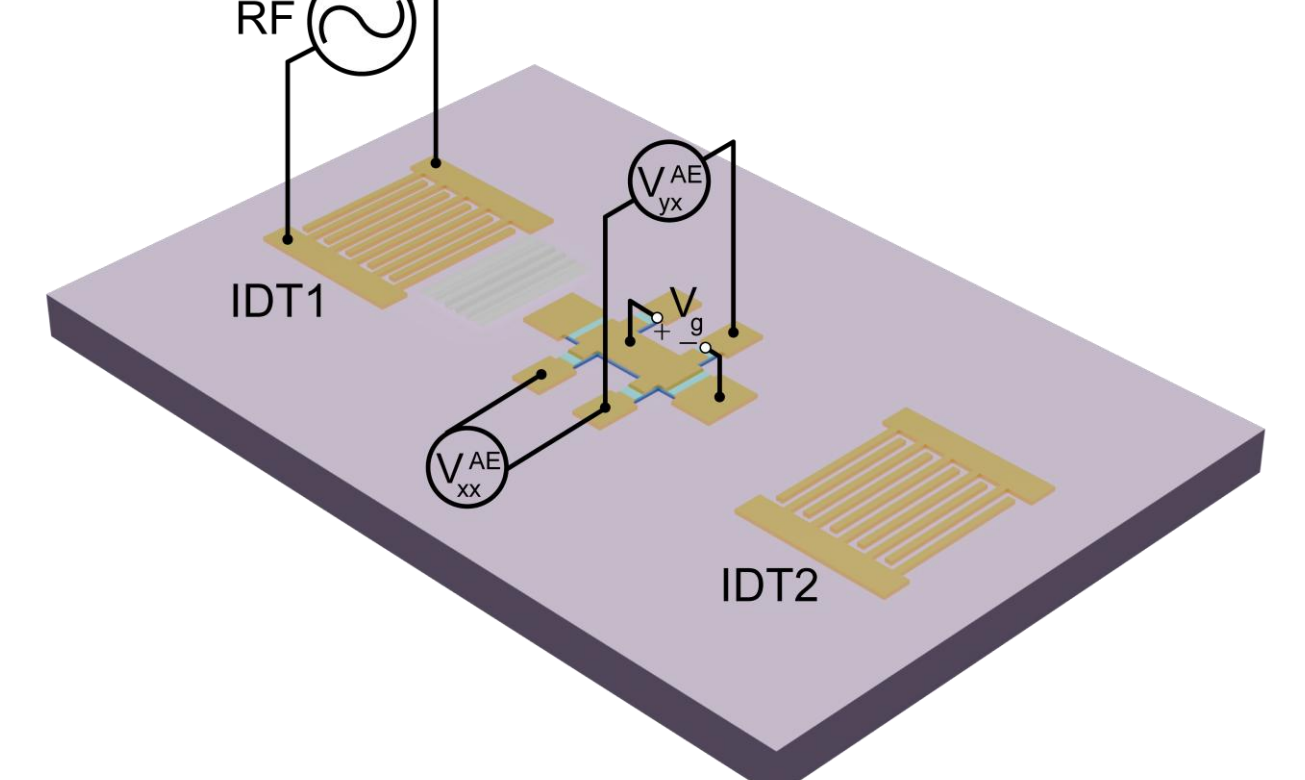
### Electrical transport & AE transport measurements



Cryogenic Superconducting Magnet System 2 K, 12 T



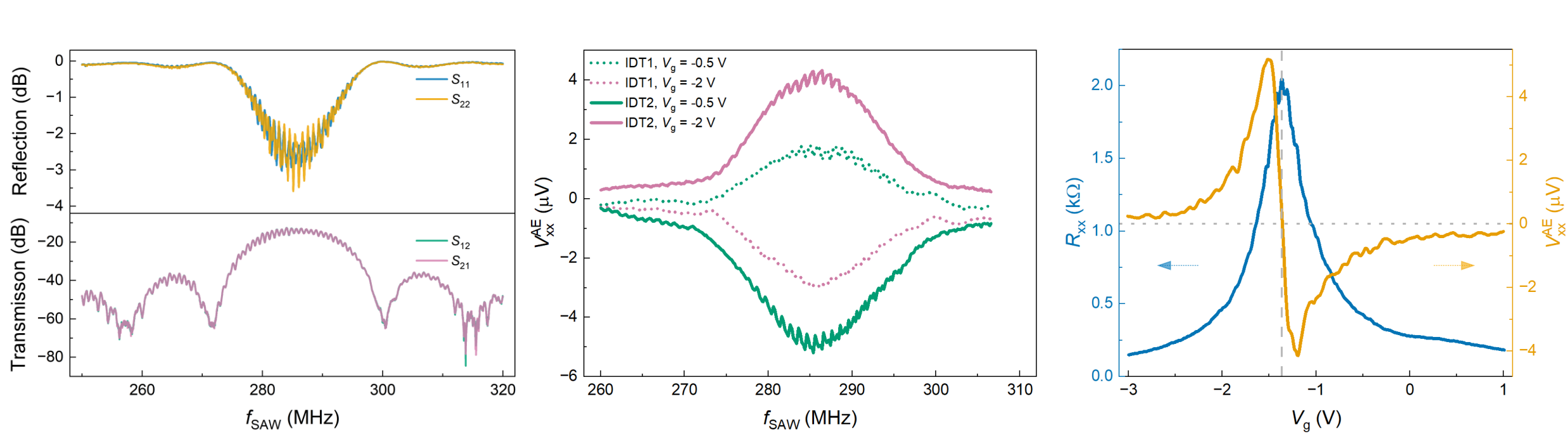
Standard four-probe configuration AC lock-in techniques



Pulsed-amplitude-modulated SAWs Open-circuit conditions

## Results

### Zero-field characterization

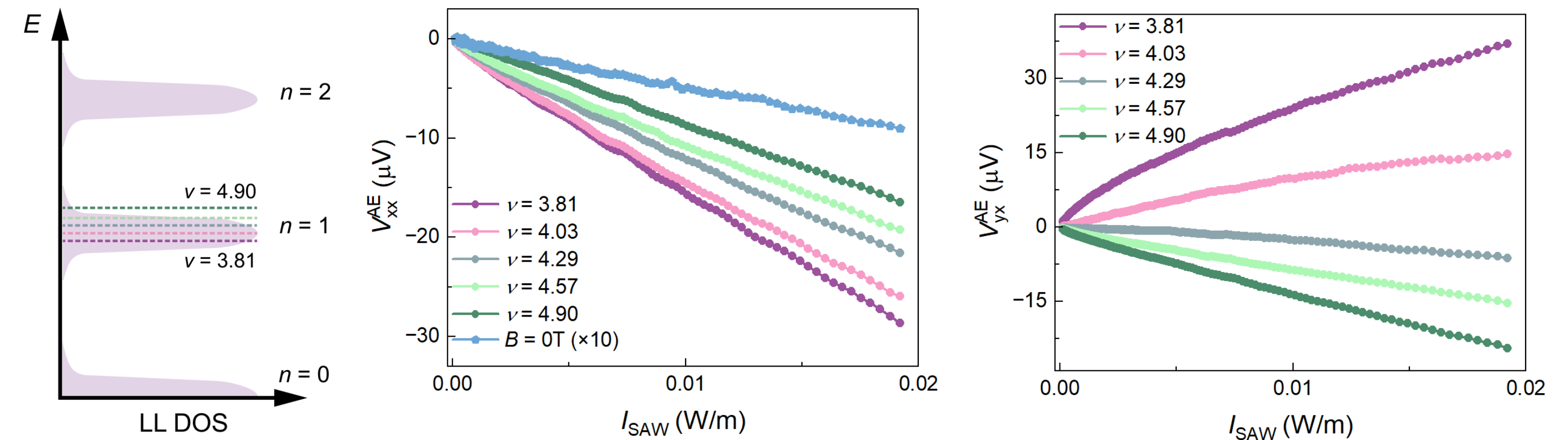


Center frequency ~285.5 MHz

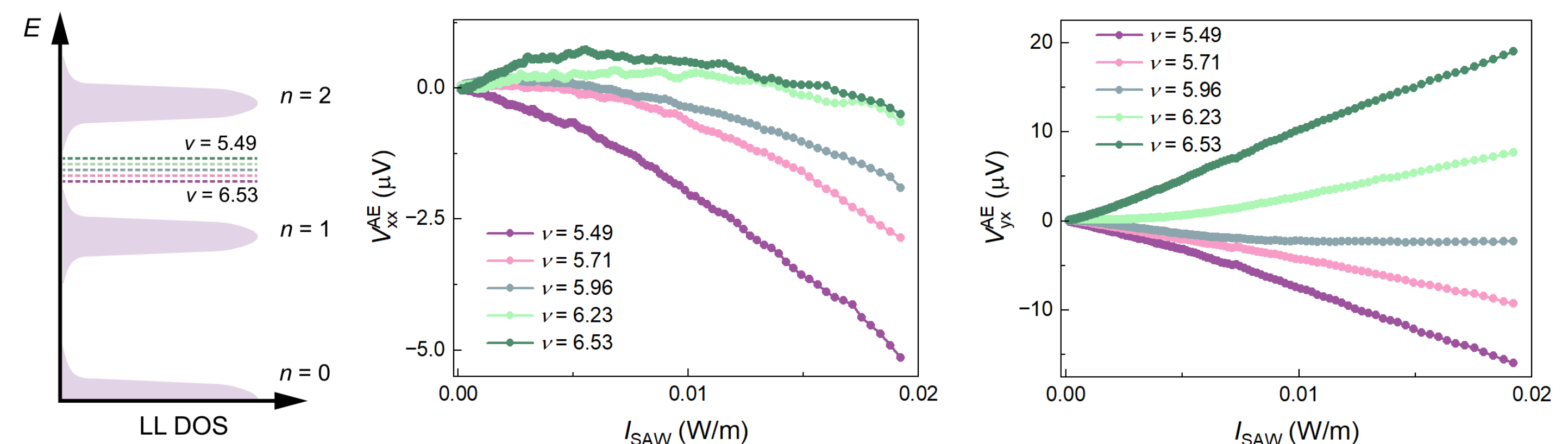
$$\text{SAW relaxation model}$$

$$J_{xx}^{AE} = -\frac{\pi K^2 I \sigma_m (n_e - n_h)}{e \lambda v (n_e + n_h)^2} V_g$$

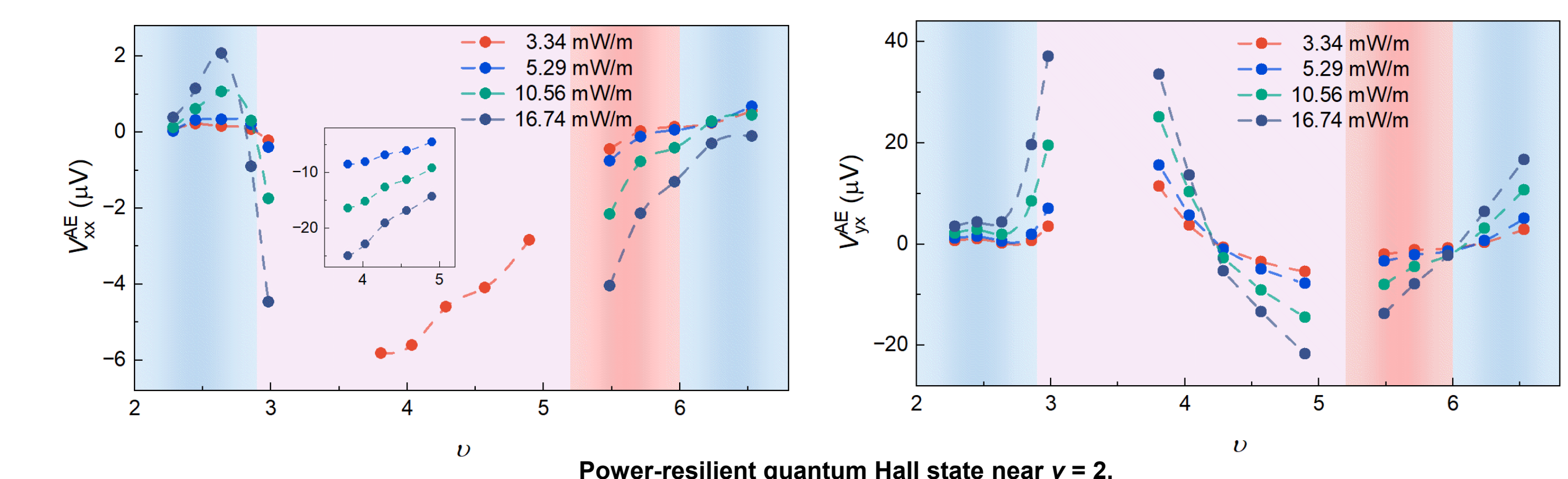
### Power-dependent AE transport in metallic and QH regimes



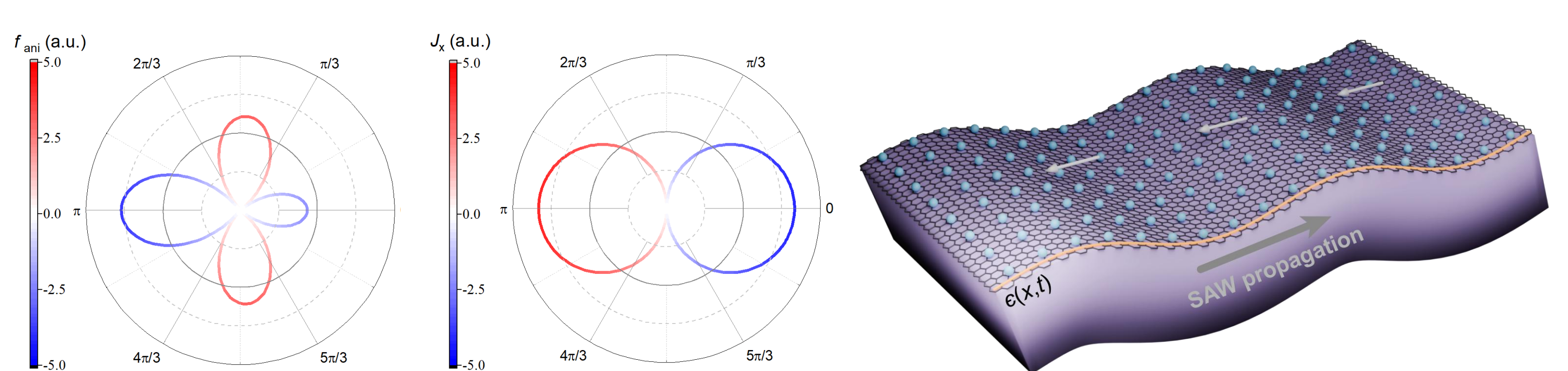
Linear scaling of AE voltages with SAW intensity in the metallic regime confirms the classical acoustic-drag model.



Quasi-electron states exhibit an anomalous polarity reversal at low power, reverting to normal electron-like transport at high power.

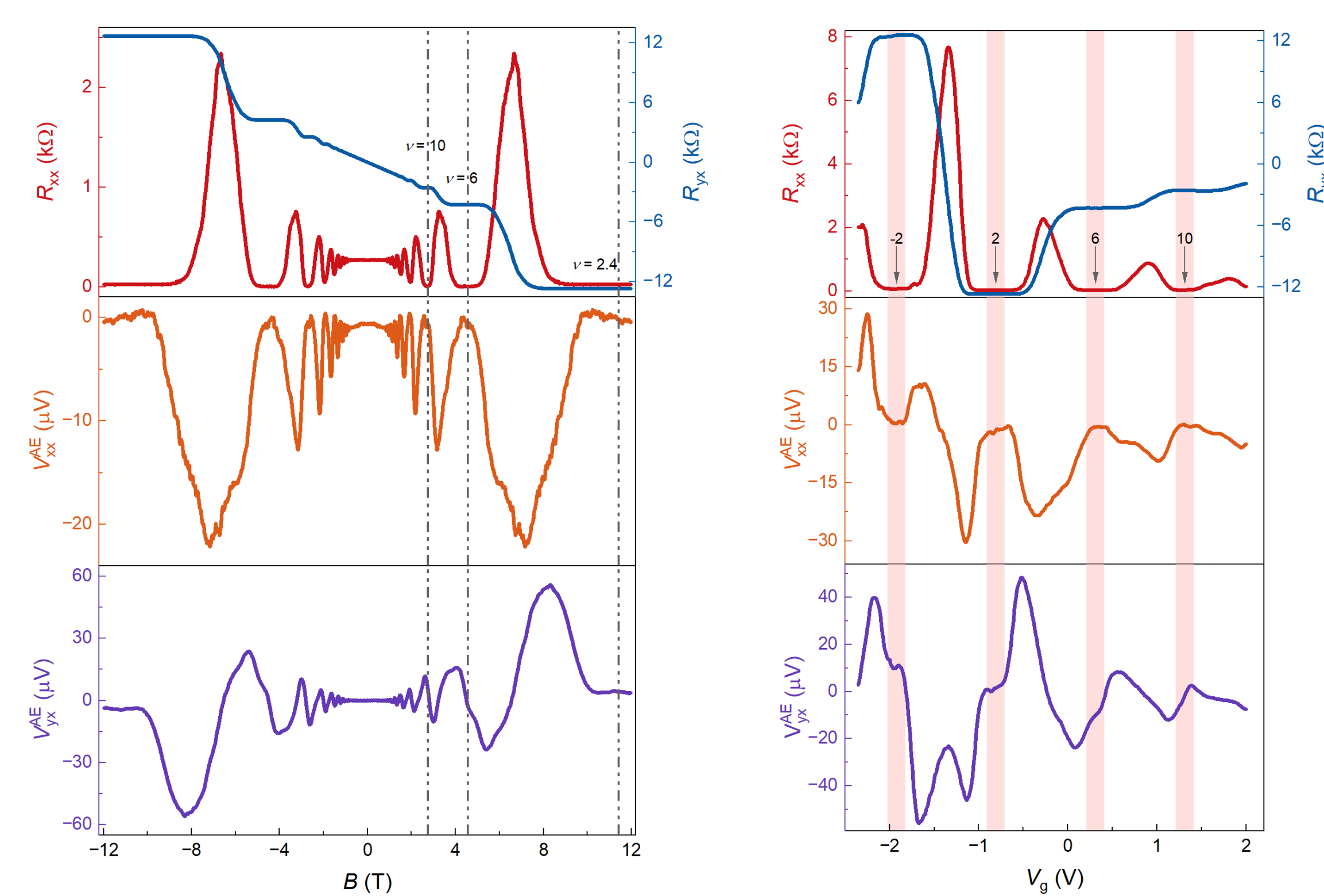


### Quadrupole-Driven Reverse AE Transport



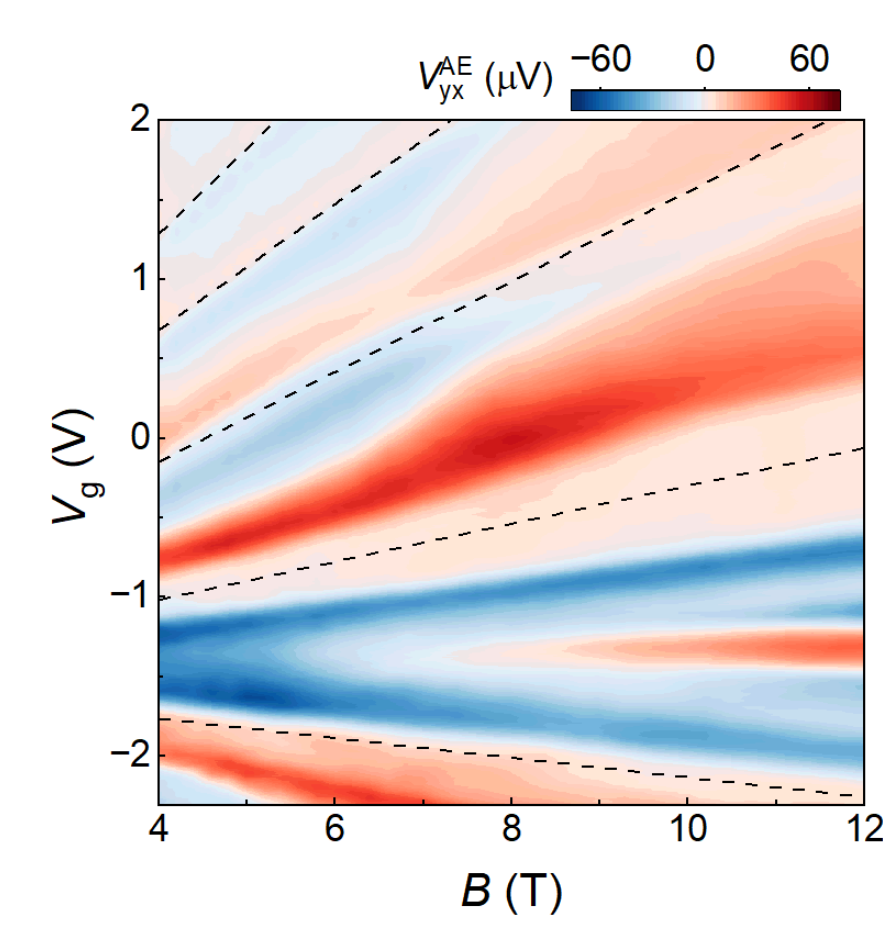
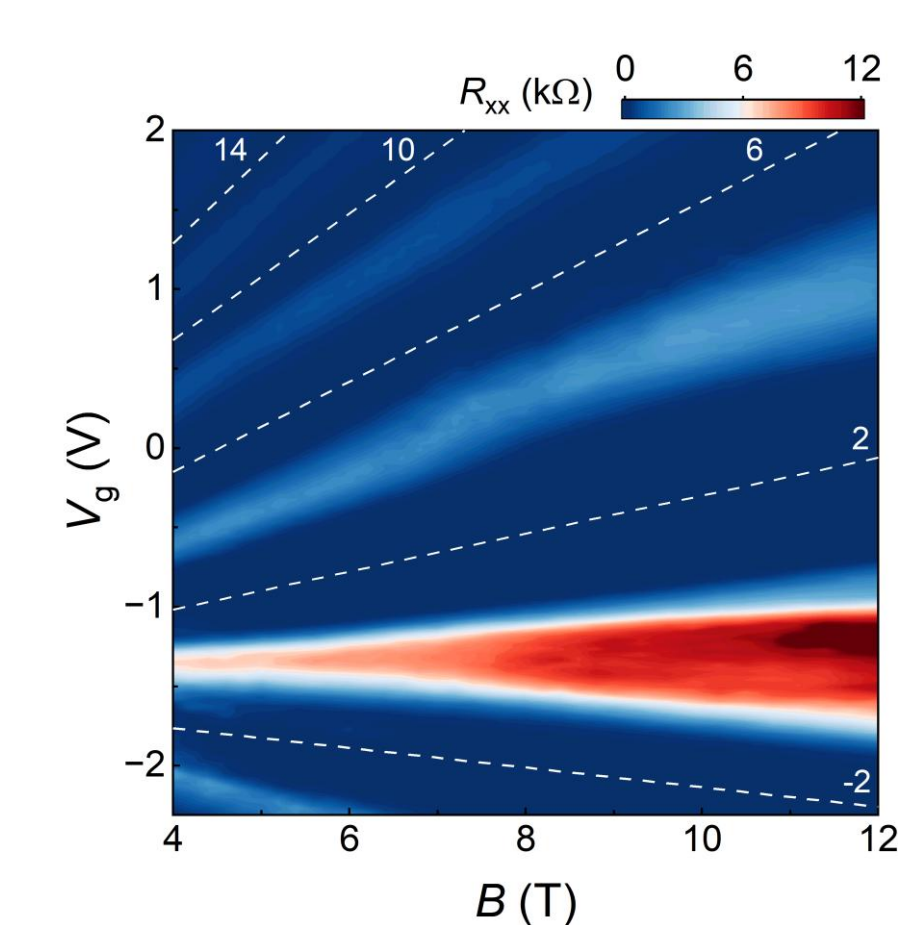
Quadrupole mode coupling ( $l = 2$ ) takes over once bulk incompressibility suppresses conventional density modulation.

### Comparing Electrical and AE Transport



Magnetic field dependence

Gate voltage dependence



Concurrence of electrical and AE transport features

## Conclusion

- Effective Landau Level Tracking:** The AE response precisely maps the evolution of quantum Hall states.
- Unveiling Quasiparticle Dynamics:** The AE response effectively captures the underlying quasiparticle dynamics within quantum Hall liquids.
- Angular Momentum Mode Coupling:** In the quantum Hall liquid, bulk incompressibility blocks conventional acoustic drag, enabling angular momentum mode coupling to drive the counter-propagating transport.

## References

- [1] Mou Y, Chen H, Liu J, et al. Gate-tunable quantum acoustoelectric transport in graphene[J]. *Nano Letters*, 2024, 24(15): 4625-4632.
- [2] Mou Y, Liu Q, Liu J, et al. Unexpected large electrostatic gating by pyroelectric charge accumulation[J]. *Nano Letters*, 2025, 25(10): 4029-4036.
- [3] Mou Y, Wang J, Chen H, et al. Coherent detection of the oscillating acoustoelectric effect in graphene[J]. *Physical Review Letters*, 2025, 134(9): 096301.
- [4] Gu J, Mou Y, Ma J, et al. Acousto-drag photovoltaic effect by piezoelectric integration of two-dimensional semiconductors[J]. *Nano Letters*, 2024, 24(33): 10322-10330.
- [5] Wang R, Liu X, Wu M, et al. Anomalous acoustocurrent within quantum Hall plateaus[J]. *Physical review letters*, 2025, 134(13): 136504.